IN THE CLAIMS

Claims 1-10 and 19-29 (Group I) have previously been cancelled without prejudice as being directed to a non-elected invention under 35 U.S.C. § 121.

Please amend claims 11, 12, 15, 30, and 37.

Please enter the pending claims, including claims 11-18 and 30-37.

1.-10 (Cancelled)

11. (Previously Presented) A method comprising:

~~exposing~~ forming a periodic pattern of alternating non-exposed lines and exposed spaces on a first photoresist, the lines having a first width;

~~exposing a portion of at least one line to radiation to break~~ breaking continuity of ~~the~~ at least one line on the first photoresist ~~and regularity of the periodic pattern~~ by positioning by means of a latent image alignment sensor an exposed region at a different wavelength with a second width ~~to expose~~ over the at least one line, the second width being greater than the first width;

~~developing the first photoresist;~~

forming a second photoresist over the first photoresist;

~~exposing an area of the second photoresist to form~~ forming a feature on the second photoresist ~~over the formerly periodic pattern of the first photoresist~~, the feature having a third width that is greater than the first width, the feature connecting two other lines from the periodic pattern that are oriented orthogonally to the feature;

~~developing the second photoresist;~~ and

etching a support using both the first photoresist and the second photoresist as a guide in a same etch step.

12. (Currently Amended) The method of Claim 11, wherein:

exposing the periodic pattern comprises exposing the first photoresist using an interference pattern having a size equal to a whole wafer; and

a pitch of the feature is greater than or equal to one and a half times a pitch of the interference pattern.

13. (Original) The method of Claim 11, wherein the radiation has a wavelength, the alternating pattern of lines and spaces having a pitch equal to about the wavelength divided by two.

14. (Original) The method of Claim 11, wherein the second photoresist is chemically distinct from the first photoresist.

15. (Currently Amended) The method of Claim 11, wherein the second photoresist is separated from the first photoresist by means of a ~~third~~ barrier layer residing between the first and second photoresists, the barrier layer having a property of sufficiently high absorption of light to prevent exposure of the first photoresist during exposure of the second photoresist and a chemical structure that prevents mixing of the first and second photoresists.

16. (Previously Presented) The method of Claim 11, wherein:

exposing the periodic pattern comprises exposing the first photoresist using an interference pattern; and

the method further comprises aligning the feature to the interference pattern.

17. (Previously Presented) The method of Claim 11, further comprising aligning the feature to be within the exposure region.

18. (Previously Presented) The method of Claim 11, wherein:

exposing the periodic pattern comprises exposing the first photoresist using an interference pattern; and

the method further comprises exposing generating a print mask by subtracting (a) a final design layout for a given layer from (b) the interference pattern.

19.-29. (Cancelled)

30. (Currently Amended) A method comprising:

receiving a pre-determined design layout;

receiving a pattern layout of alternating, parallel lines and spaces; ~~and~~

subtracting the design layout from the pattern layout of alternating, parallel lines and spaces to form a remainder layout;

resizing the remainder layout;

increasing size of expanses in a direction perpendicular to the lines and spaces; and

merging the expanses.

31. (Original) The method of Claim 30, further comprising aligning features of the design layout with at least one of the lines and spaces of the pattern layout.

32. (Original) The method of Claim 30, further comprising generating a machine-readable description of a print mask with the remainder layout.

33. (Original) The method of Claim 30, further comprising generating a print mask with the remainder layout.

34. (Previously Presented) The method of Claim 30, further comprising resizing features of the remainder layout.

35. (Previously Presented) The method of Claim 30, wherein the pattern layout comprises the layout of a pattern produced by interference lithography.

36. (Previously Presented) The method of Claim 30, wherein etching the support comprises transferring the feature and at least some of the spaces into the support.

37. (Currently Amended) A method comprising:

exposing a periodic pattern of alternating non-exposed lines and exposed spaces on a first photoresist using interference lithography, the periodic pattern having a size equal to a whole wafer, the lines having a first width;

exposing a portion of at least one line to radiation at a different wavelength to break continuity of the line and regularity of the periodic pattern by positioning an exposed region by means of a latent image alignment sensor with a second width to expose the at least one line, the second width being greater than the first width;

developing the first photoresist;

forming a second photoresist over the first photoresist;

exposing an area of the second photoresist to form a feature over the ~~formerly~~ periodic pattern of the first photoresist, the feature having a third width that is greater than the first width, the feature connecting two other lines from the periodic pattern that are oriented orthogonally to the feature;

developing the second photoresist; and

etching a support to transfer the feature and at least some of the spaces to the support.